

# Qing-Tai Zhao

## List of Publications by Year in descending order

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docs citations

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times ranked

1604  
citing authors

#	ARTICLE	IF	CITATIONS
1	Inverters With Strained Si Nanowire Complementary Tunnel Field-Effect Transistors. IEEE Electron Device Letters, 2013, 34, 813-815.	2.2	171
2	Tuning of NiSi <sup>δ</sup> -Si Schottky barrier heights by sulfur segregation during Ni silicidation. Applied Physics Letters, 2005, 86, 062108.	1.5	127
3	Effective Schottky barrier lowering in silicon-on-insulator Schottky-barrier metal-oxide-semiconductor field-effect transistors using dopant segregation. Applied Physics Letters, 2005, 87, 263505.	1.5	81
4	Strained Si and SiGe Nanowire Tunnel FETs for Logic and Analog Applications. IEEE Journal of the Electron Devices Society, 2015, 3, 103-114.	1.2	70
5	An Improved Si Tunnel Field Effect Transistor With a Buried Strained $\text{Si}_{1-x}\text{Ge}_x$ Source. IEEE Electron Device Letters, 2011, 32, 1480-1482.	2.2	68
6	Impact of TFET Unidirectionality and Ambipolarity on the Performance of 6T SRAM Cells. IEEE Journal of the Electron Devices Society, 2015, 3, 223-232.	1.2	68
7	Line and Point Tunneling in Scaled Si/SiGe Heterostructure TFETs. IEEE Electron Device Letters, 2014, 35, 699-701.	2.2	62
8	Negative Capacitance as Performance Booster for Tunnel FETs and MOSFETs: An Experimental Study. IEEE Electron Device Letters, 2017, 38, 1485-1488.	2.2	62
9	Ultrathin Ni Silicides With Low Contact Resistance on Strained and Unstrained Silicon. IEEE Electron Device Letters, 2010, 31, 350-352.	2.2	57
10	Fabrication and Characterization of Enhancement-Mode High- $\kappa$ $\text{LaLuO}_3$ -AlGaIn/GaN MIS-HEMTs. IEEE Transactions on Electron Devices, 2013, 60, 3040-3046.	1.6	46
11	Complementary Strained Si GAA Nanowire TFET Inverter With Suppressed Ambipolarity. IEEE Electron Device Letters, 2016, 37, 950-953.	2.2	46
12	Artificial Synapses Based on Ferroelectric Schottky Barrier Field-Effect Transistors for Neuromorphic Applications. ACS Applied Materials & Interfaces, 2021, 13, 32005-32012.	4.0	43
13	$\Omega$ -Gated Silicon and Strained Silicon Nanowire Array Tunneling FETs. IEEE Electron Device Letters, 2012, 33, 1535-1537.	2.2	42
14	Demonstration of improved transient response of inverters with steep slope strained Si NW TFETs by reduction of TAT with pulsed I-V and NW scaling. , 2013, , .		41
15	AlGaIn/GaN MISHEMTs With High- $\kappa$ $\text{LaLuO}_3$ Gate Dielectric. IEEE Electron Device Letters, 2012, 33, 979-981.	2.2	40
16	Novel SiGe/Si line tunneling TFET with high Ion at low Vdd and constant SS. , 2015, , .		38
17	Nanometer patterning of epitaxial $\text{CoSi}_2/\text{Si}(100)$ for ultrashort channel Schottky barrier metal-oxide-semiconductor field effect transistors. Applied Physics Letters, 1999, 74, 454-456.	1.5	37
18	Schottky barrier height modulation using dopant segregation in schottky-barrier SOI-MOSFETs. , 0, , .		37

#	ARTICLE	IF	CITATIONS
19	Experimental demonstration of strained Si nanowire GAA n-TFETs and inverter operation with complementary TFET logic at low supply voltages. Solid-State Electronics, 2016, 115, 152-159.	0.8	32
20	Effect of hysteretic and non-hysteretic negative capacitance on tunnel FETs DC performance. Nanotechnology, 2018, 29, 095202.	1.3	32
21	Strained Silicon Complementary TFET SRAM: Experimental Demonstration and Simulations. IEEE Journal of the Electron Devices Society, 2018, 6, 1033-1040.	1.2	29
22	2-D Physics-Based Compact DC Modeling of Double-Gate Tunnel-FETs. IEEE Transactions on Electron Devices, 2019, 66, 132-138.	1.6	29
23	Tunneling field-effect transistor with a strained Si channel and a Si <sub>0.5</sub> Ge <sub>0.5</sub> source. Solid-State Electronics, 2012, 74, 97-101.	0.8	27
24	Dislocation-Based Si-Nanodevices. Japanese Journal of Applied Physics, 2010, 49, 04DJ02.	0.8	26
25	Measurement of effective electron mass in biaxial tensile strained silicon on insulator. Applied Physics Letters, 2009, 95, .	1.5	25
26	Impact of Gate-Source Overlap on the Device/Circuit Analog Performance of Line TFETs. IEEE Transactions on Electron Devices, 2019, 66, 4081-4086.	1.6	24
27	Influences of substrates and substrate temperatures on characteristics of epitaxial La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> thin films. Thin Solid Films, 1998, 323, 304-308.	0.8	23
28	Radio-Frequency Study of Dopant-Segregated n-Type SB-MOSFETs on Thin-Body SOI. IEEE Electron Device Letters, 2010, 31, 537-539.	2.2	23
29	Characteristics of Recessed-Gate TFETs With Line Tunneling. IEEE Transactions on Electron Devices, 2018, 65, 769-775.	1.6	22
30	Electrical characterization of strained and unstrained silicon nanowires with nickel silicide contacts. Nanotechnology, 2010, 21, 105701.	1.3	21
31	Epitaxial growth of Ni(Al)Si <sub>0.7</sub> Ge <sub>0.3</sub> on Si <sub>0.7</sub> Ge <sub>0.3</sub> /Si(100) by Al interlayer mediated epitaxy. Applied Physics Letters, 2011, 98, 252101.	1.5	20
32	Schottky barrier tuning via dopant segregation in NiGeSn-GeSn contacts. Journal of Applied Physics, 2017, 121, .	1.1	20
33	NiSi <sub>2</sub> /Si interface chemistry and epitaxial growth mode. Acta Materialia, 2009, 57, 232-236.	3.8	19
34	Formation of steep, low Schottky-barrier contacts by dopant segregation during nickel silicidation. Journal of Applied Physics, 2010, 107, 044510.	1.1	19
35	High mobility compressive strained Si <sub>0.5</sub> Ge <sub>0.5</sub> quantum well p-MOSFETs with higher-k/metal-gate. Solid-State Electronics, 2011, 62, 185-188.	0.8	19
36	Fabrication of epitaxial CoSi <sub>2</sub> nanowires. Applied Physics Letters, 2001, 79, 824-826.	1.5	18

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37	Low Temperature Deposition of High-k/Metal Gate Stacks on High-Sn Content (Si)GeSn-Alloys. ACS Applied Materials & Interfaces, 2016, 8, 13133-13139.	4.0	18
38	Simulation of Fabricated 20-nm Schottky Barrier MOSFETs on SOI: Impact of Barrier Lowering. IEEE Transactions on Electron Devices, 2012, 59, 1320-1327.	1.6	17
39	Fabrication of Schottky barrier MOSFETs on SOI by a self-assembly CoSi <sub>2</sub> -patterning method. Solid-State Electronics, 2003, 47, 1183-1186.	0.8	16
40	Segregation of ion implanted sulfur in Si(100) after annealing and nickel silicidation. Journal of Applied Physics, 2007, 102, .	1.1	15
41	Hole Mobilities of $\text{Si/Si}_{0.5}\text{Ge}_{0.5}$ Quantum-Well Transistor on SOI and Strained SOI. IEEE Electron Device Letters, 2012, 33, 758-760.	2.2	15
42	Impact of strain and Ge concentration on the performance of planar SiGe band-to-band-tunneling transistors. Solid-State Electronics, 2012, 71, 42-47.	0.8	15
43	Line Tunneling Dominating Charge Transport in SiGe/Si Heterostructure TFETs. IEEE Transactions on Electron Devices, 2016, 63, 4173-4178.	1.6	14
44	Improved NiSi <sub>0.8</sub> Ge <sub>0.2</sub> /Si <sub>0.8</sub> Ge <sub>0.2</sub> Contacts by C+ Pre-Implantation. Electrochemical and Solid-State Letters, 2011, 14, H261.	2.2	13
45	Electrical characterization of $\hat{\Gamma}$ -gated uniaxial tensile strained Si nanowire-array metal-oxide-semiconductor field effect transistors with $\langle 100 \rangle$ - and $\langle 110 \rangle$ - channel orientations. Thin Solid Films, 2012, 520, 3332-3336.	0.8	13
46	Impact of Si cap, strain and temperature on the hole mobility of (s)Si/sSiGe/(s)SOI quantum-well p-MOSFETs. Microelectronic Engineering, 2014, 113, 5-9.	1.1	13
47	Benchmarking of Homojunction Strained-Si NW Tunnel FETs for Basic Analog Functions. IEEE Transactions on Electron Devices, 2017, 64, 1441-1448.	1.6	13
48	A Novel Gate-Normal Tunneling Field-Effect Transistor With Dual-Metal Gate. IEEE Journal of the Electron Devices Society, 2018, 6, 1070-1076.	1.2	13
49	Diameter Scaling of Vertical Ge Gate- All-Around Nanowire pMOSFETs. IEEE Transactions on Electron Devices, 2020, 67, 2988-2994.	1.6	13
50	Vertical Ge Gate-All-Around Nanowire pMOSFETs With a Diameter Down to 20 nm. IEEE Electron Device Letters, 2020, 41, 533-536.	2.2	13
51	Characterization of high- $\hat{\Gamma}$ LaLuO <sub>3</sub> thin film grown on AlGaIn/GaN heterostructure by molecular beam deposition. Applied Physics Letters, 2011, 99, 182103.	1.5	12
52	Epitaxial GeSn/Ge Vertical Nanowires for p-Type Field-Effect Transistors with Enhanced Performance. ACS Applied Nano Materials, 2021, 4, 94-101.	2.4	12
53	Ultrathin epitaxial Ni-silicide contacts on (1 0 0) Si and SiGe: Structural and electrical investigations. Microelectronic Engineering, 2013, 107, 190-195.	1.1	11
54	Subthreshold Behavior of Floating-Gate MOSFETs With Ferroelectric Capacitors. IEEE Transactions on Electron Devices, 2018, 65, 4641-4645.	1.6	10

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55	Rare-Earth Scandate/TiN Gate Stacks in SOI MOSFETs Fabricated With a Full Replacement Gate Process. IEEE Transactions on Electron Devices, 2011, 58, 617-622.	1.6	9
56	Electrical and Structural Properties of Ternary Rare-Earth Oxides on Si and Higher Mobility Substrates and their Integration as High-k Gate Dielectrics in MOSFET Devices. ECS Transactions, 2011, 35, 461-479.	0.3	9
57	Hole Transport in Strained $\text{Si}_{0.5}\text{Ge}_{0.5}$ QW-MOSFETs With $\langle 110 \rangle$ and $\langle 100 \rangle$ Channel Orientations. IEEE Electron Device Letters, 2012, 33, 1105-1107.	2.2	9
58	Ultrathin highly uniform Ni(Al) germanosilicide layer with modulated B8 type $\text{Ni}_5(\text{SiGe})_3$ phase formed on strained $\text{Si}_{1-x}\text{Ge}_x$ layers. Applied Physics Letters, 2013, 103, .	1.5	9
59	Experimental demonstration of improved analog device performance of nanowire-TFETs. Solid-State Electronics, 2015, 113, 179-183.	0.8	9
60	Experimental $I_{\text{on}} \sim V(T)$ and $C \sim V$ Analysis of Si Planar p-TFETs on Ultrathin Body. IEEE Transactions on Electron Devices, 2016, 63, 5036-5040.	1.6	9
61	A T-Shaped SOI Tunneling Field-Effect Transistor With Novel Operation Modes. IEEE Journal of the Electron Devices Society, 2019, 7, 1114-1118.	1.2	9
62	Structural characteristics and the control of crystallographic orientation of $\text{CeO}_2$ thin films prepared by laser ablation. Nuclear Instruments & Methods in Physics Research B, 1998, 135, 535-539.	0.6	8
63	Full silicidation process for making $\text{CoSi}_2$ on $\text{SiO}_2$ . Applied Physics Letters, 2004, 84, 3292-3294.	1.5	8
64	Strained Silicon on Wafer Level by Waferbonding: Materials Processing, Strain Measurements and Strain Relaxation. ECS Transactions, 2008, 16, 311-320.	0.3	8
65	Experimental demonstration of improved analog device performance in GAA-NW-TFETs. , 2014, , .		8
66	Implementation of a DC compact model for double-gate Tunnel-FET based on 2D calculations and application in circuit simulation. , 2016, , .		8
67	Schottky barrier height modulation by Arsenic Dopant segregation. , 2008, , .		7
68	Correlation of Bandgap Reduction with Inversion Response in (Si)GeSn/High-k/Metal Stacks. ACS Applied Materials & Interfaces, 2017, 9, 9102-9109.	4.0	7
69	Transient negative capacitance and charge trapping in FDSOI MOSFETs with ferroelectric $\text{HfYOx}$ . Solid-State Electronics, 2019, 159, 71-76.	0.8	7
70	Steep Switching Si Nanowire p-FETs With Dopant Segregated Silicide Source/Drain at Cryogenic Temperature. IEEE Electron Device Letters, 2022, 43, 1187-1190.	2.2	7
71	Fabrication of Schottky barrier MOSFETs using self-assembly $\text{CoSi}_2$ nanopatterning and spacer gate technologies. Microelectronic Engineering, 2003, 70, 186-190.	1.1	6
72	Gate-all-around Si nanowire array tunnelling FETs with high on-current of $75 \text{ mA}/\mu\text{m}$ @ $V_{\text{DD}} = 1.1\text{V}$ . , 2013, , .		6

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73	SiGe on SOI nanowire array TFETs with homo- and heterostructure tunnel junctions. , 2013, , .		6
74	Analysis of GeSn-SiGeSn hetero-tunnel FETs. , 2014, , .		6
75	Damage formation in Si(100) induced by MeV self-ion implantation. Nuclear Instruments & Methods in Physics Research B, 1993, 82, 575-578.	0.6	5
76	Growth of ferroelectric (K <sub>0.5</sub> Na <sub>0.5</sub> ) <sub>0.2</sub> (Sr <sub>0.75</sub> Ba <sub>0.25</sub> ) <sub>0.9</sub> Nb <sub>2</sub> O <sub>6</sub> thin films by pulsed laser deposition. Solid State Communications, 1997, 103, 285-289.	0.9	5
77	Nanopatterning of epitaxial CoSi <sub>2</sub> using oxidation in a local stress field and fabrication of nanometer metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2004, 96, 5775-5780.	1.1	5
78	Schottky-barrier height tuning of Ni and Pt germanide/n-Ge contacts using dopant segregation. , 2008, , .		5
79	Enhancement-Mode LaLuO <sub>3</sub> â€“AlGaIn/GaN Metalâ€“Insulatorâ€“Semiconductor High-Electron-Mobility Transistors Using Fluorine Plasma Ion Implantation. Japanese Journal of Applied Physics, 2013, 52, 08JN02.	0.8	5
80	Experimental demonstration of inverter and NAND operation in p-TFET logic at ultra-low supply voltages down to $V_{DD}$ ; 0.15 V. , 2014, , .		5
81	Experimental Investigation on Alloy Scattering in sSi <sub>0.5</sub> mGe <sub>0.5</sub> /sSOI Quantum-Well p-MOSFET. IEEE Transactions on Electron Devices, 2014, 61, 950-952.	1.6	5
82	High performance strained Si <sub>0.5</sub> Ge <sub>0.5</sub> quantum-well p-MOSFETs fabricated using a high-Îº/metal-gate last process. Superlattices and Microstructures, 2015, 83, 210-215.	1.4	5
83	Analog and RF analysis of gate all around silicon nanowire MOSFETs. , 2017, , .		5
84	Experimental examination of tunneling paths in SiGe/Si gate-normal tunneling field-effect transistors. Applied Physics Letters, 2017, 111, .	1.5	5
85	Damage accumulation and amorphization in GaAs by MeV Si <sup>+</sup> ion implantation at different tilt angles. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 415-418.	0.6	4
86	Longitudinal and transverse moments of the distribution of MeV Ti ions implanted in Si measured by SIMS. Journal Physics D: Applied Physics, 1995, 28, 1158-1161.	1.3	4
87	Reduction of secondary defects in 50 keV P <sup>+</sup> -implanted Si(100) by MeV Si ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1996, 108, 81-84.	0.6	4
88	Ion beam defect engineering in semiconductors and optoelectric materials. Nuclear Instruments & Methods in Physics Research B, 1996, 115, 421-429.	0.6	4
89	Growth, Patterning and Microelectronic Applications of Epitaxial Cobaltdisilicide. Materials Research Society Symposia Proceedings, 1998, 514, 145.	0.1	4
90	Self-assembly patterning of epitaxial CoSi <sub>2</sub> nano-structures. Microelectronic Engineering, 2002, 64, 443-447.	1.1	4

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91	Thermal stability of CoSi <sub>2</sub> layers implemented in a silicon-on-insulator substrate. Semiconductor Science and Technology, 2006, 21, 157-161.	1.0	4
92	MOSFETs with high mobility channel materials and higher-k/metal gate stack. , 2010, , .		4
93	Comparison of strained SiGe heterostructure-on-insulator (001) and (110) PMOSFETs: C <sub>60</sub> characteristics, mobility, and ON current. Solid-State Electronics, 2011, 65-66, 64-71.	0.8	4
94	Si/SiGe hetero-structure tunneling field effect transistors with in-situ doped SiGe source. , 2012, , .		4
95	Mobility Enhancement and Gate-Induced-Drain-Leakage Analysis of Strained-SiGe Channel p-MOSFETs with Higher- $\epsilon_r$ LaLuO <sub>3</sub> Gate Dielectric. Chinese Physics Letters, 2014, 31, 016101.	1.3	4
96	Strained Si nanowire GAA n-TFETs for low supply voltages. , 2015, , .		4
97	Ultrathin homogeneous Ni(Al) germanosilicide layer formation on strained SiGe with Al/Ni multi-layers. Microelectronic Engineering, 2015, 137, 88-91.	1.1	4
98	Lateral straggling of Hg <sup>+</sup> in both amorphized quartz crystal and Ni film by RBS. Physics Letters, Section A: General, Atomic and Solid State Physics, 1990, 150, 277-280.	0.9	3
99	Range profiles of Xe ions at energies from 50 to 400 keV in potassium titanyl phosphate. Physics Letters, Section A: General, Atomic and Solid State Physics, 1990, 151, 241-245.	0.9	3
100	Channeling study on damage in potassium titanyl phosphate induced by ion irradiation. Physical Review B, 1994, 50, 770-776.	1.1	3
101	Epitaxial growth and electrical transport properties of La <sub>0.5</sub> Sr <sub>0.5</sub> CoO <sub>3</sub> thin films prepared by pulsed laser deposition. Science in China Series A: Mathematics, 1999, 42, 865-872.	0.5	3
102	High performance Schottky barrier MOSFETs on UTB SOI. , 2009, , .		3
103	Performance enhancement of uniaxially-tensile strained Si NW-nFETs fabricated by lateral strain relaxation of SSOI. , 2009, , .		3
104	Impact of strain and Ge concentration on the performance of planar SiGe band-to-band-tunneling transistors. , 2011, , .		3
105	Rare-earth oxide/TiN gate stacks on high mobility strained silicon on insulator for fully depleted metal-oxide-semiconductor field-effect transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 01A903.	0.6	3
106	Nanowire and planar UTB SOI Schottky Barrier MOSFETs with dopant segregation. , 2012, , .		3
107	Si based tunnel field effect transistors: Recent achievements. , 2013, , .		3
108	Investigation of band-to-band tunneling parameters in sige by using MOSFET GIDL current analysis. , 2014, , .		3

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109	Improved LDMOS performance with buried multi-finger gates. Microelectronic Engineering, 2014, 122, 29-32.	1.1	3
110	Improved NiSi contacts on Si by CF4 plasma immersion ion implantation for 14nm node MOSFETs. , 2015, , .		3
111	Experimental Investigation of $\{C\}$ $\hat{=}$ $\{V\}$ Characteristics of Si Tunnel FETs. IEEE Electron Device Letters, 2017, 38, 818-821.	2.2	3
112	Range profiles of xenon in PVA. Nuclear Instruments & Methods in Physics Research B, 1990, 47, 351-354.	0.6	2
113	Lattice disorder in silicon induced by 2.0 MeV Cu+ irradiation. Applied Physics A: Solids and Surfaces, 1992, 55, 332-334.	1.4	2
114	Range profiles of implanted argon ions in polymers. Radiation Effects and Defects in Solids, 1994, 128, 287-293.	0.4	2
115	Effects of MeV Si ion irradiation on the properties of shallow P+N junctions. Nuclear Instruments & Methods in Physics Research B, 1998, 135, 280-284.	0.6	2
116	Schottky-barrier height tuning using dopant segregation in Schottky-barrier MOSFETs on fully-depleted SOI. Materials Research Society Symposia Proceedings, 2006, 913, 1.	0.1	2
117	Epitaxial growth of NiSi2 induced by sulfur segregation at the NiSi2/Si(100) interface. Journal of Materials Research, 2009, 24, 135-139.	1.2	2
118	Formation and characterization of ultra-thin Ni silicides on strained and unstrained silicon. , 2010, , .		2
119	NiSi nano-contacts to strained and unstrained silicon nanowires. , 2011, , .		2
120	Tunneling field-effect transistor with a strained Si channel and a $\text{Si}_{0.5}\text{Ge}_{0.5}$ source. , 2011, , .		2
121	Lanthanum Lutetium oxide integration in a gate-first process on SOI MOSFETs. , 2011, , .		2
122	20nm Gate length Schottky MOSFETs with ultra thin NiSi/epitaxial NiSi $\text{Ge}_{0.5}$ source/drain. , 2011, , .		2
123	Si tunneling transistors with high on-currents and slopes of 50 mV/dec using segregation doped NiSi $\text{Ge}_{0.5}$ tunnel junctions. , 2012, , .		2
124	Formation of a highly Erbium doped silicon-on-insulator layer by introducing SiOx on or into a silicon surface. Nuclear Instruments & Methods in Physics Research B, 2012, 278, 1-3.	0.6	2
125	Low frequency noise in strained silicon nanowire array MOSFETs and Tunnel-FETs. , 2013, , .		2
126	Effects of C+ ion implantation on electrical properties of NiSiGe/SiGe contacts. Nuclear Instruments & Methods in Physics Research B, 2013, 307, 408-411.	0.6	2

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127	Ultrathin Ni silicide contacts on Si and SiGe formed with multi thin Ni/Al layers. , 2014, , .		2
128	Tunnel-FET inverters for ultra-low power logic with supply voltage down to $V_{DD}$ &#x003D; 0.2 V. , 2014, , .		2
129	Homogeneous NiSi $_{1-x}$ Ge $_x$ layer formation on strained SiGe with ultrathin Ni layers. Microelectronic Engineering, 2015, 139, 26-30.	1.1	2
130	Experimental demonstration of planar SiGe on Si TFETs with counter doped pocket. , 2015, , .		2
131	Silicon GAA NW TFET inverters with suppressed ambipolarity. , 2016, , .		2
132	Static noise margin analysis of 8T TFET SRAM cells using a 2D compact model adapted to measurement data of fabricated TFET devices. , 2017, , .		2
133	Phase evolution of ultra-thin Ni silicide films on CF $_4$ plasma immersion ion implanted Si. Nanotechnology, 2020, 31, 205201.	1.3	2
134	4-Terminal Ferroelectric Schottky Barrier Field Effect Transistors as Artificial Synapses. , 2021, , .		2
135	RBS studies of the lattice damage caused by 1 Me V Si $^+$ implantation into Al $_0.3$ Ga $_0.7$ As/GaAs superlattices at elevated temperature. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 392-395.	0.6	1
136	Ion-beam-induced solid phase crystallization of MeV Si $^{+}$ -implanted Si(100). Acta Physica Sinica (overseas Edition), 1995, 4, 118-124.	0.1	1
137	Nanometer patterning of epitaxial CoSi $_2$ /Si(100) by local oxidation. Solid-State Electronics, 1999, 43, 1091-1094.	0.8	1
138	Large current enhancement in n-MOSFETs with strained Si on insulator. , 2007, , .		1
139	Strained silicon nanowire array MOSFETs with high- $k$ /metal gate stack. , 2012, , .		1
140	Using platinum silicide as a superconductor for silicon electron coolers. , 2013, , .		1
141	Strained silicon nanowire tunnel FETs and NAND logic. , 2014, , .		1
142	High on-currents with highly strained Si nanowire MOSFETs. , 2014, , .		1
143	Si based tunnel FETs : Status and perspectives. , 2014, , .		1
144	Ion-sensitive field-effect transistor with sSi/Si $_0.5$ Ge $_0.5$ /sSOI quantum-well for high voltage sensitivity. Microelectronic Engineering, 2016, 163, 115-118.	1.1	1

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145	Damage profiles in silicon induced by 1.0 MeV Ti ions at tilted angle incidence. Physics Letters, Section A: General, Atomic and Solid State Physics, 1992, 166, 361-364.	0.9	0
146	Two-dimensional distributions of Xe ions implanted in Si <sub>3</sub> N <sub>4</sub> films. Vacuum, 1993, 44, 1045-1048.	1.6	0
147	Dechannelling analysis of damage in Si created by MeV Ti ions. Journal Physics D: Applied Physics, 1994, 27, 571-573.	1.3	0
148	Damage behavior of silicon by MeV Ge <sup>+</sup> irradiation under tilted angle. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 3027.	1.6	0
149	Investigation of depth distributions of defects in Si created by high energy Ti ions. Vacuum, 1994, 45, 955-958.	1.6	0
150	Reduction of secondary defects and diffusion of B atoms in BF <sub>2</sub> -implanted Si(100) by ion-beam defect engineering. , 0, , .		0
151	Fabrication of nanometer Schottky-tunneling MOSFETs by a novel silicide nanopatterning method. , 1999, , .		0
152	Properties of ion implanted epitaxial CoSi <sub>2</sub> /Si(1 0 0) after rapid thermal oxidation. Nuclear Instruments & Methods in Physics Research B, 2000, 164-165, 1004-1009.	0.6	0
153	Self-Assembly CoSi <sub>2</sub> -Nanostructures for Fabrication of Schottky Barrier MOSFETs on SOI. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
154	Nickel silicidation on sulfur implanted Si(100). , 2008, , .		0
155	Interfacial and electrical characterization of HfO <sub>2</sub> gate dielectric film with a blocking layer of Al <sub>2</sub> O <sub>3</sub> . , 2009, , .		0
156	High mobility Si-Ge channels and novel high-k materials for nanomofets. , 2010, , .		0
157	Electrical Characterization of TbScO <sub>3</sub> /TiN Gate Stacks of MOS Capacitors and MOSFETs on Strained and Unstrained SOI. ECS Transactions, 2010, 33, 195-202.	0.3	0
158	Non-linear analysis of n-type Schottky-Barrier MOSFETs. , 2010, , .		0
159	Si Nanowire tunnel FETs with epitaxial NiSi <sub>2</sub> source/drain and dopant segregation. , 2012, , .		0
160	Characteristics of higher- $\kappa$ dielectric LaLuO <sub>3</sub> with TiN as gate stack. , 2012, , .		0
161	Strained Si nanowire tunnel FETs and inverters. , 2013, , .		0
162	Si based tunneling field effect transistors and inverters. , 2013, , .		0

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163	Equivalent Trap Energy Level Extraction for SiGe Using Gate-Induced-Drain-Leakage Current Analysis. Chinese Physics Letters, 2014, 31, 106103.	1.3	0
164	Multi-gates SOI LDMOS for improved on-state performance. , 2014, , .		0
165	Si n-TFETs on ultra thin body with suppressed ambipolarity. , 2016, , .		0
166	Ultrathin lateral unidirectional bipolar-type insulated-gate transistor as pH sensor. , 2017, , .		0
167	Experimental $I-V$ and $C-V$ Analysis of Schottky-Barrier Metal-Oxide-Semiconductor Field Effect Transistors with Epitaxial NiSi <sub>2</sub> Contacts and Dopant Segregation. Chinese Physics Letters, 2017, 34, 078501.	1.3	0
168	Impact of Al addition on the formation of Ni germanosilicide layers under different temperature annealing *. Chinese Physics B, 2017, 26, 098503.	0.7	0
169	Impact of gate to source/drain alignment on the static and RF performance of junctionless Si nanowire n-MOSFETs. Solid-State Electronics, 2020, 169, 107817.	0.8	0